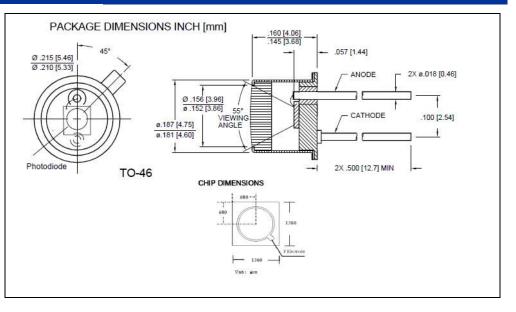
InGaAs Photodetector

PRELIMINARY SD039-151-011

Precision – Control – Results



Advanced Photonix. Inc



DESCRIPTION

The **SD039-151-011** is a high sensitivity, low noise, 1 mm diameter active area InGaAs photodiode (chip dimensions 1.36mmx1.36mm) for detection at SWIR, NIR wavelengths for imaging and sensing applications. Photodetector assembled in a TO-46 package.

FEATURES

- Low Noise,
- High Sensitivity
- Detection at SWIR and NIR

RELIABILITY

This API high-reliability detector is in principle able to meet military test requirements (Mil-STD-750, Mil-STD-883) after proper screening and group test.

Contact API for recommendations on specific test conditions and procedures.

ABSOLUTE MAXIMUM RATINGS

APPLICATIONS

- Industrial Sensing
- Security and Defense
- Communication
- Medical

$T_a = 23^{\circ}C$ non condensing

1/16 inch from case for 3 seconds max

| SYMBOL | MIN | MAX | UNITS |
|-----------------------|-----|------|-------|
| Reverse Voltage | - | 40 | V |
| Operating Temperature | -40 | +100 | °C |
| Storage Temperature | -55 | +125 | °C |
| Soldering Temperature | - | +260 | °C |

Information in this technical datasheet is believed to

be correct and reliable. However, no responsibility is

assumed for possible inaccuracies or omission.

Specifications are subject to change without notice.

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InGaAs Photodetector



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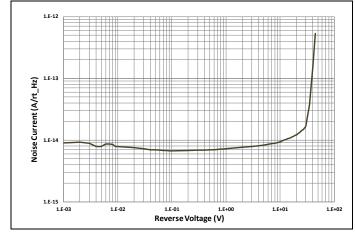
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Precision – Control – Results

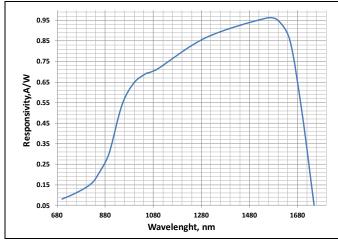
| ELECTRO-OPTICAL CHARACTERISTICS RATINGS | | $T_a = 23^{\circ}C$ unless noted otherwise | | | | | |
|---|---|--|-------------------------|------|--------|--|--|
| PARAMETER | TEST CONDITIONS | MIN | ТҮР | MAX | UNITS | | |
| Breakdown Voltage | $I_{\text{bias}} = 1 \ \mu A$ | 20 | - | 40 | V | | |
| Spectral Range | _ | 800 | - | 1700 | nm | | |
| Responsivity | λ= 1310 nm,Vr=5V | 0.8 | 0.9 | - | A/W | | |
| Shunt Resistance | $V_{\text{bias}} = 10 \text{ mV}$ | 40 | 200 | - | MΩ | | |
| Dark Current | $V_{\text{bias}} = 5V$ | - | 0.2 | 10 | nA | | |
| Capacitance | $V_{\text{bias}} = 5V; f = 1.0 \text{ MHz}$ | - | 70 | 150 | pF | | |
| Rise Time (50 Ω load) | $V_{bias} = 5V; \lambda = 1310 \text{ nm}$ | - | 2.0 | - | ns | | |
| Noise Equivalent Power | Vr= 5V@ λ=1310 | - | 1.0x10 ⁻¹⁴ - | - | fW/√Hz | | |
| | | | | | | | |

TYPICAL PERFORMANCE

NOISE CURRENT vs. REVERSE BIAS



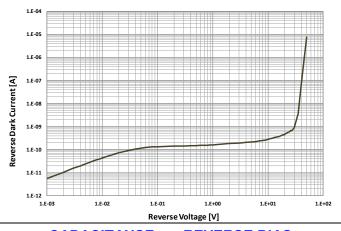
SPECTRAL RESPONSE



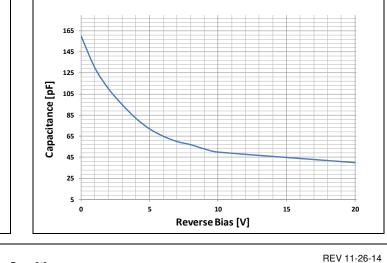
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DARK CURRENT vs. REVERSE BIAS







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